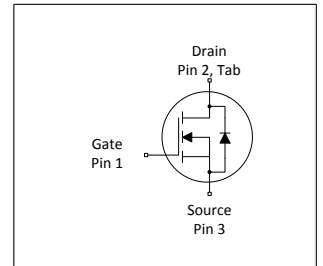
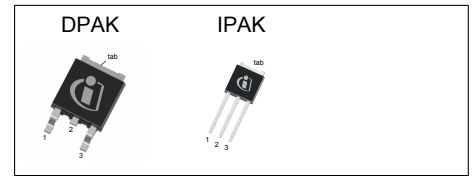


MOSFET

600V CoolMOS™ CE Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.



Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV and indoor lighting.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	2100	$m\Omega$
I_d	3.7	A
$Q_{g,typ}$	6.7	nC
$I_{D,pulse}$	6	A
$E_{oss@400V}$	0.76	μJ

Type / Ordering Code	Package	Marking	Related Links
IPD60R2K1CE	PG-TO 252	60S2K1CE	see Appendix A
IPU60R2K1CE	PG-TO 251		

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	3.7 2.4	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	6	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	11	mJ	$I_D=0.4\text{A}$; $V_{DD}=50\text{V}$; see table 11
Avalanche energy, repetitive	E_{AR}	-	-	0.06	mJ	$I_D=0.4\text{A}$; $V_{DD}=50\text{V}$; see table 11
Avalanche current, repetitive	I_{AR}	-	-	0.4	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots480\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation TO-251, TO252	P_{tot}	-	-	38	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-40	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-40	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	2.7	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	6	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 9
Maximum diode commutation speed	di/dt	-	-	500	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 9

2 Thermal characteristics

Table 3 Thermal characteristics TO-251, TO-252

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.26	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	$^\circ\text{C/W}$	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	$^\circ\text{C}$	1.6mm (0.063 in.) from case for 10s

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.50$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V, I_D=0.25mA$
Gate threshold voltage	$V_{(GS)th}$	2.5	3.0	3.5	V	$V_{DS}=V_{GS}, I_D=0.06mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=600, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.80 4.68	2.10 -	Ω	$V_{GS}=10V, I_D=0.76A, T_j=25^\circ C$ $V_{GS}=10V, I_D=0.76A, T_j=150^\circ C$
Gate resistance	R_G	-	12	-	Ω	$f=1MHz, \text{open drain}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	140	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Output capacitance	C_{oss}	-	12	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	8.5	-	pF	$V_{GS}=0V, V_{DS}=0...480V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	30	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...480V$
Turn-on delay time	$t_{d(on)}$	-	7	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=0.9A,$ $R_G=12.2\Omega; \text{see table 10}$
Rise time	t_r	-	7	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=0.9A,$ $R_G=12.2\Omega; \text{see table 10}$
Turn-off delay time	$t_{d(off)}$	-	30	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=0.9A,$ $R_G=12.2\Omega; \text{see table 10}$
Fall time	t_f	-	50	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=0.9A,$ $R_G=12.2\Omega; \text{see table 10}$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	0.8	-	nC	$V_{DD}=480V, I_D=0.9A, V_{GS}=0 \text{ to } 10V$
Gate to drain charge	Q_{gd}	-	3.6	-	nC	$V_{DD}=480V, I_D=0.9A, V_{GS}=0 \text{ to } 10V$
Gate charge total	Q_g	-	6.7	-	nC	$V_{DD}=480V, I_D=0.9A, V_{GS}=0 \text{ to } 10V$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=480V, I_D=0.9A, V_{GS}=0 \text{ to } 10V$

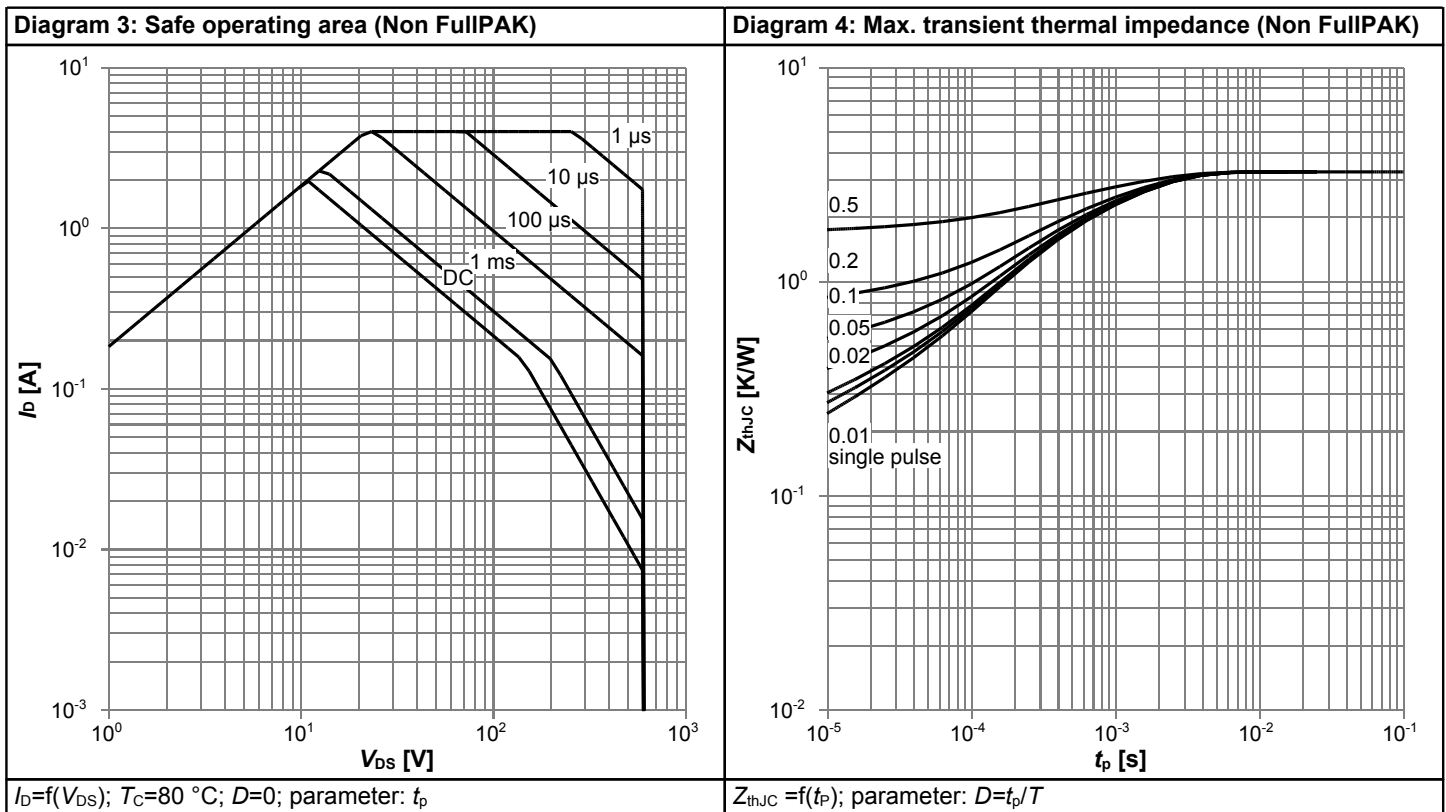
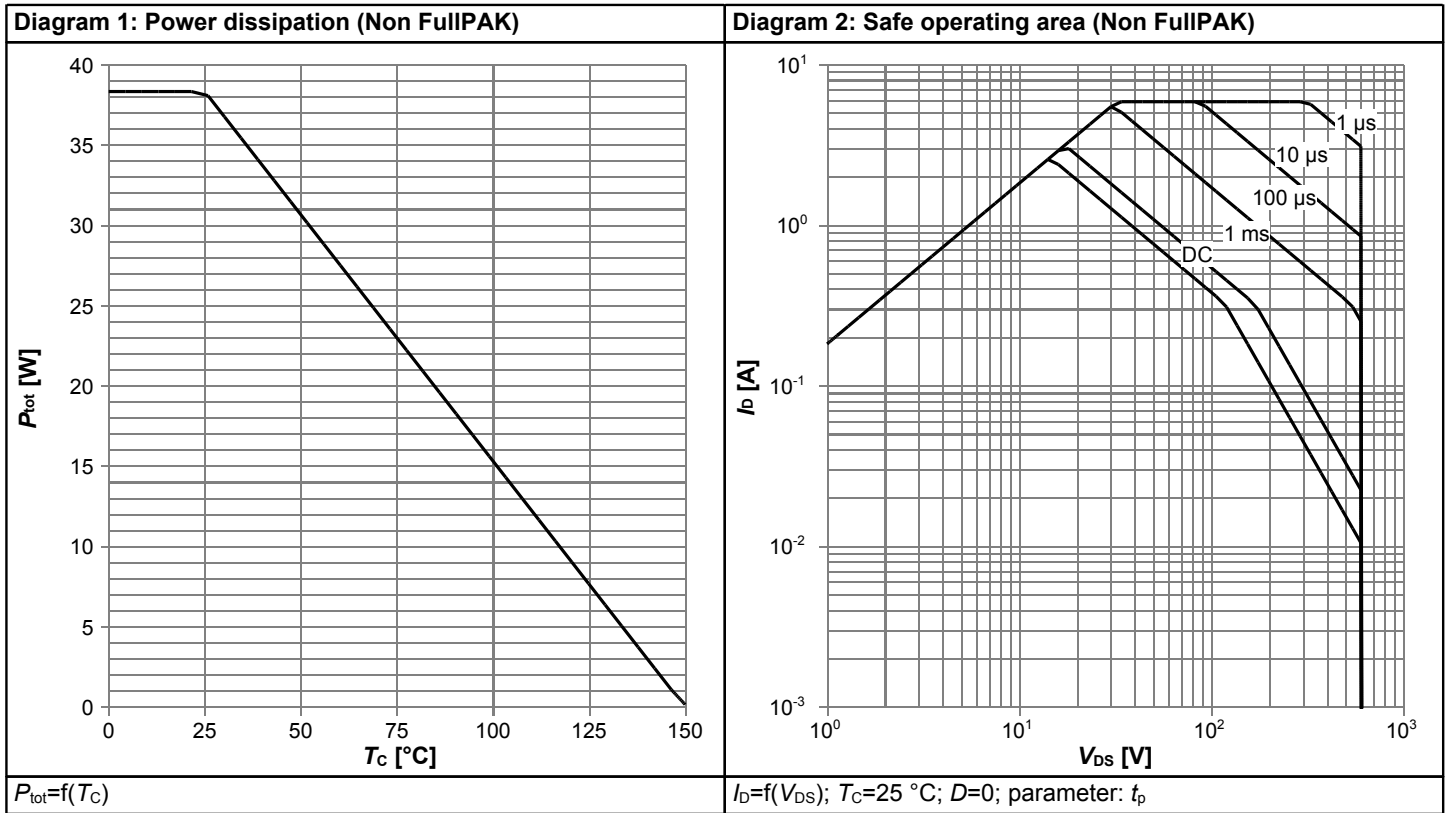
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=0.9A, T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	180	-	ns	$V_R=400V, I_F=0.9A, di_F/dt=100A/\mu s$; see table 9
Reverse recovery charge	Q_{rr}	-	0.67	-	μC	$V_R=400V, I_F=0.9A, di_F/dt=100A/\mu s$; see table 9
Peak reverse recovery current	I_{rrm}	-	7.1	-	A	$V_R=400V, I_F=0.9A, di_F/dt=100A/\mu s$; see table 9

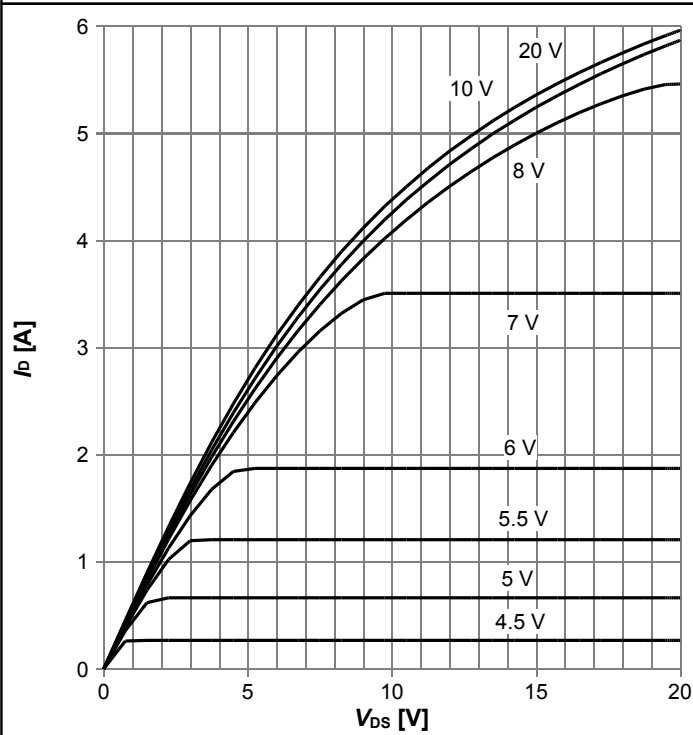
4 Electrical characteristics diagrams



600V CoolMOS™ CE Power Transistor

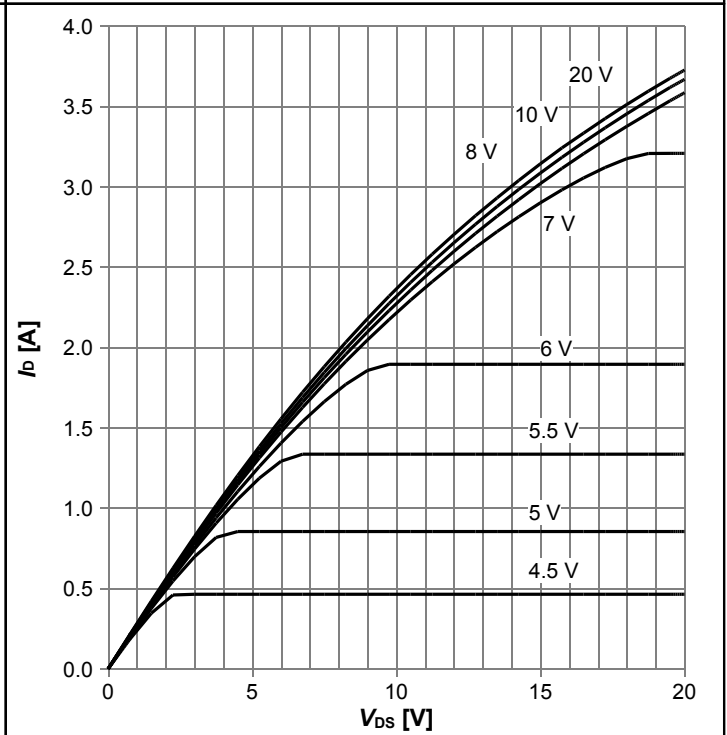
IPD60R2K1CE, IPU60R2K1CE

Diagram 5: Typ. output characteristics



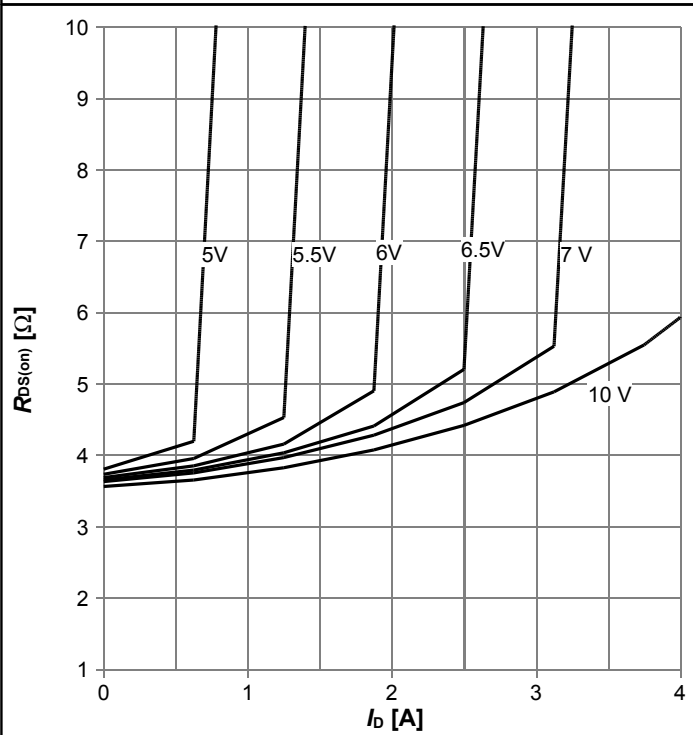
$I_D=f(V_{DS}); T_j=25\text{ °C};$ parameter: V_{GS}

Diagram 6: Typ. output characteristics



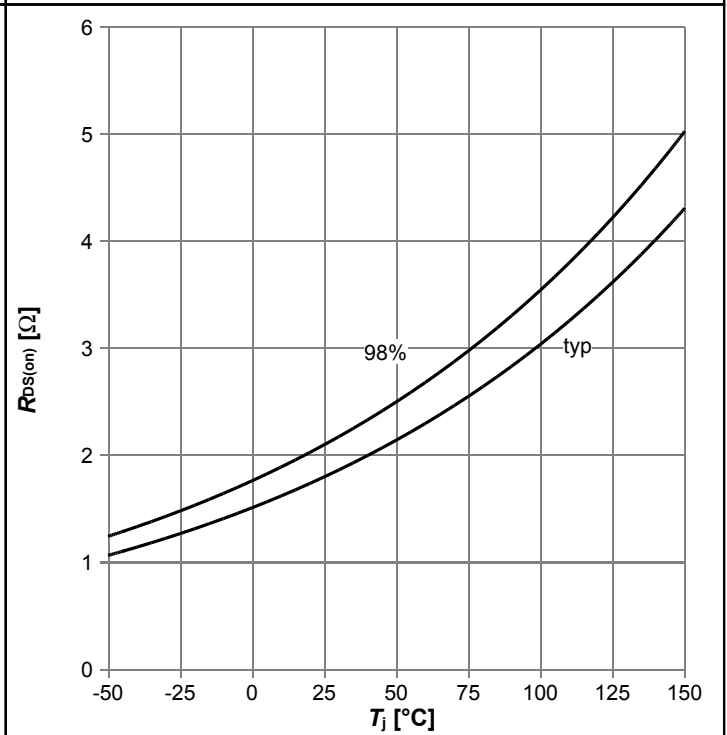
$I_D=f(V_{DS}); T_j=125\text{ °C};$ parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D); T_j=125\text{ °C};$ parameter: V_{GS}

Diagram 8: Drain-source on-state resistance

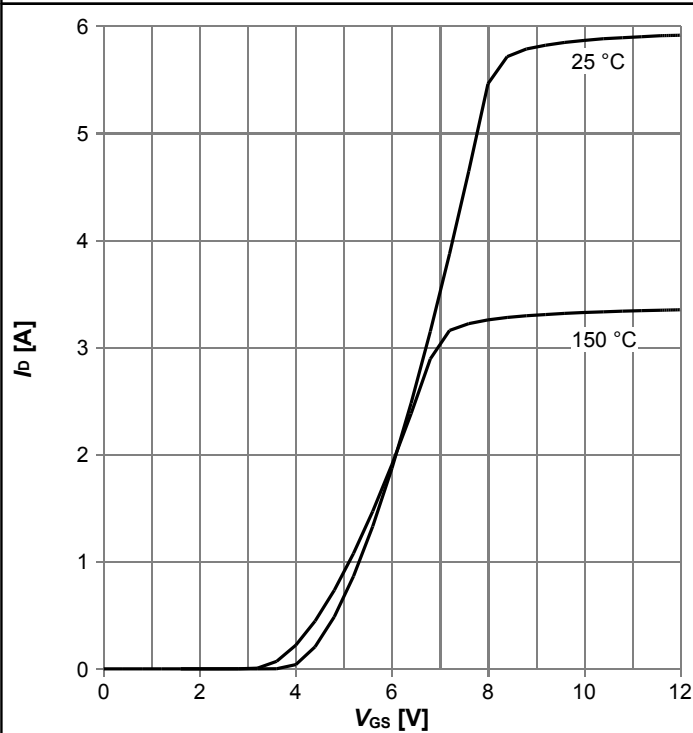


$R_{DS(on)}=f(T_j); I_D=0.76\text{ A}; V_{GS}=10\text{ V}$

600V CoolMOS™ CE Power Transistor

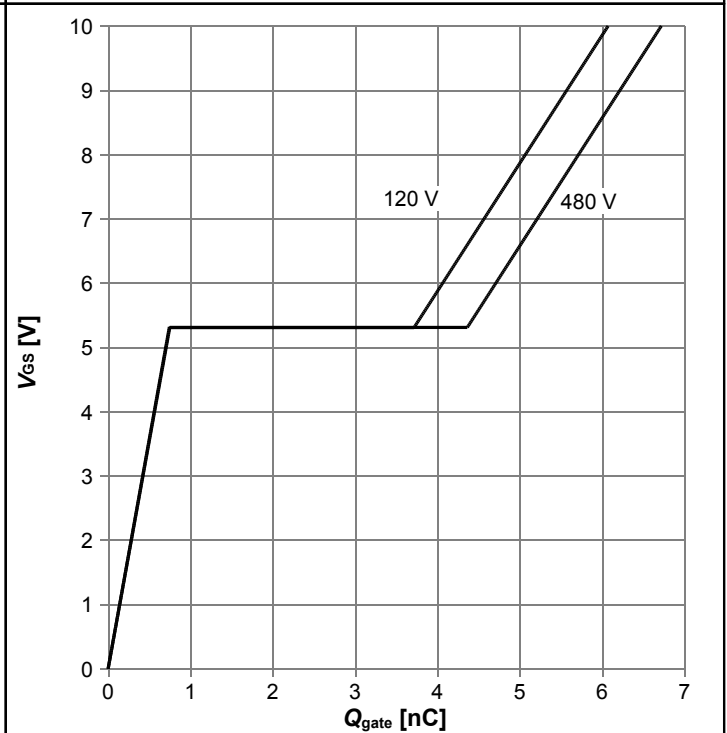
IPD60R2K1CE, IPU60R2K1CE

Diagram 9: Typ. transfer characteristics



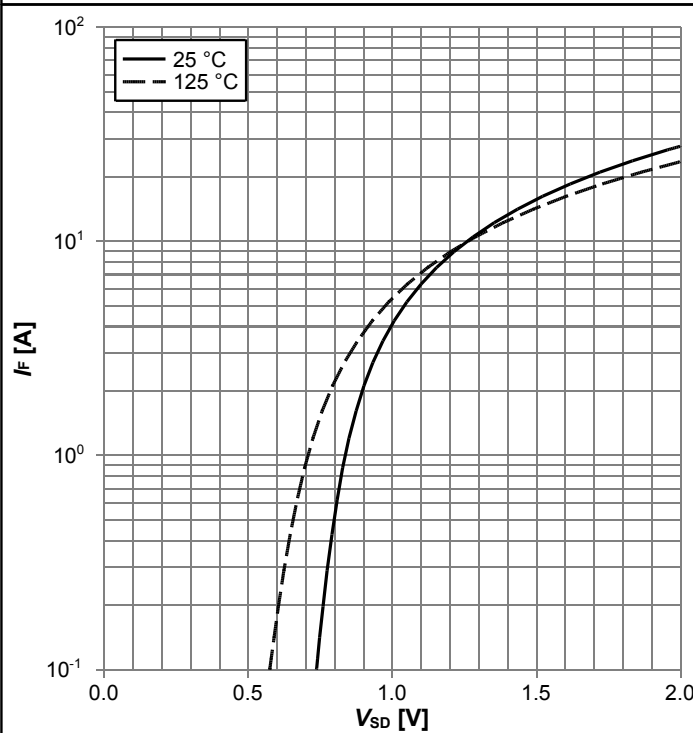
$I_D=f(V_{GS}); V_{DS}=20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



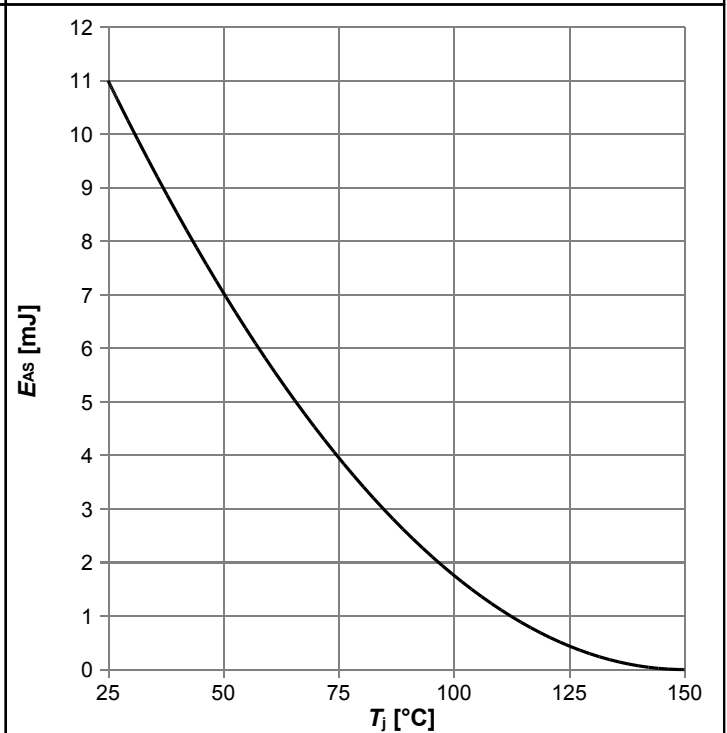
$V_{GS}=f(Q_{gate}); I_D=0.9 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



$I_F=f(V_{SD}); \text{parameter: } T_j$

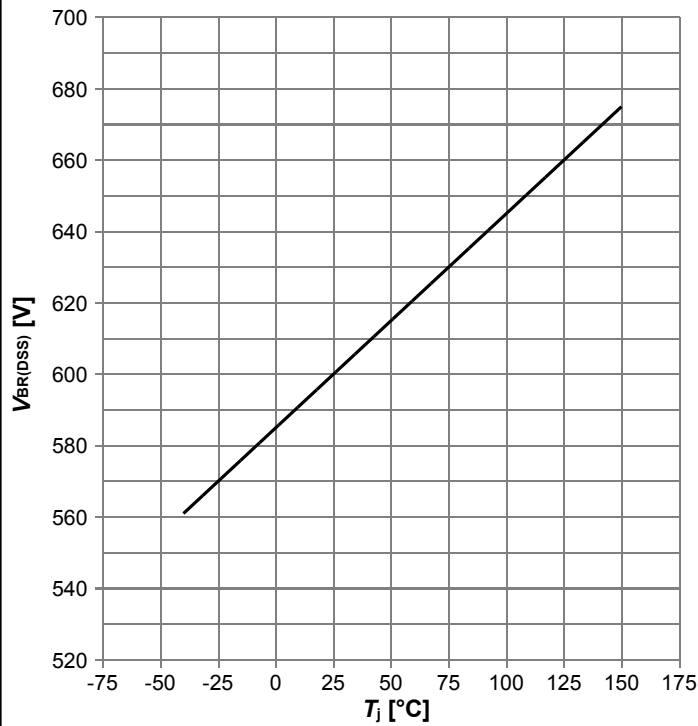
Diagram 12: Avalanche energy



$E_{AS}=f(T_j); I_D=0.4 \text{ A}; V_{DD}=50 \text{ V}$

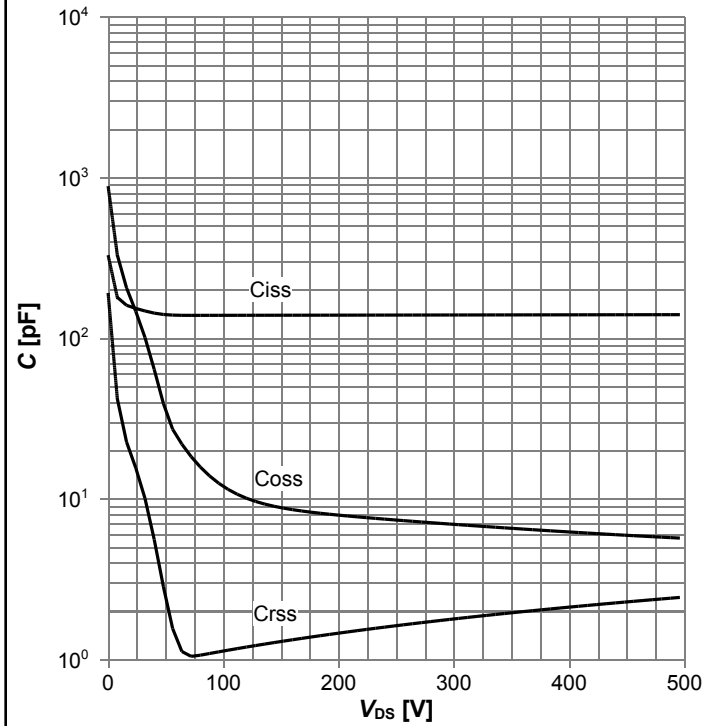
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Diagram 13: Drain-source breakdown voltage



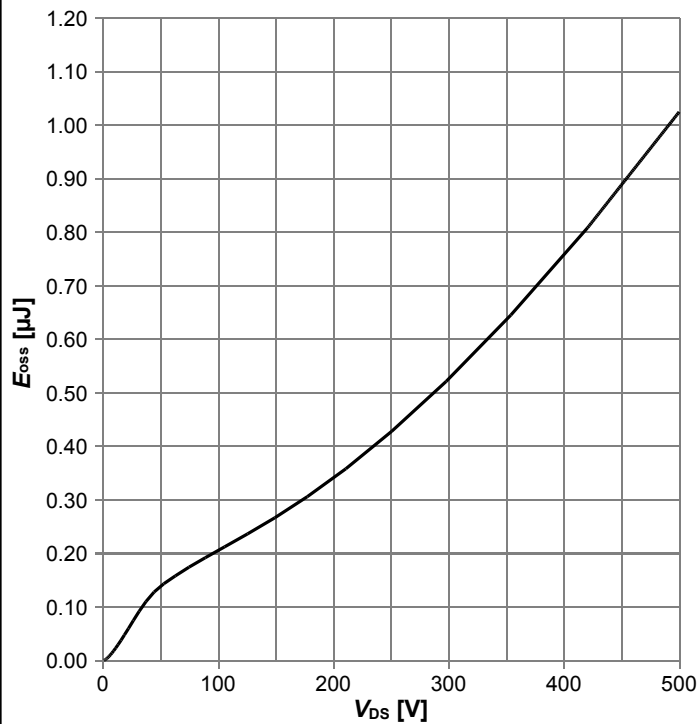
$V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0 \text{ V}; f=1 \text{ MHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
<p>$R_{g1} = R_{g2}$</p>	<p>$t_{tr} = t_F + t_S$ $Q_{tr} = Q_F + Q_S$</p>

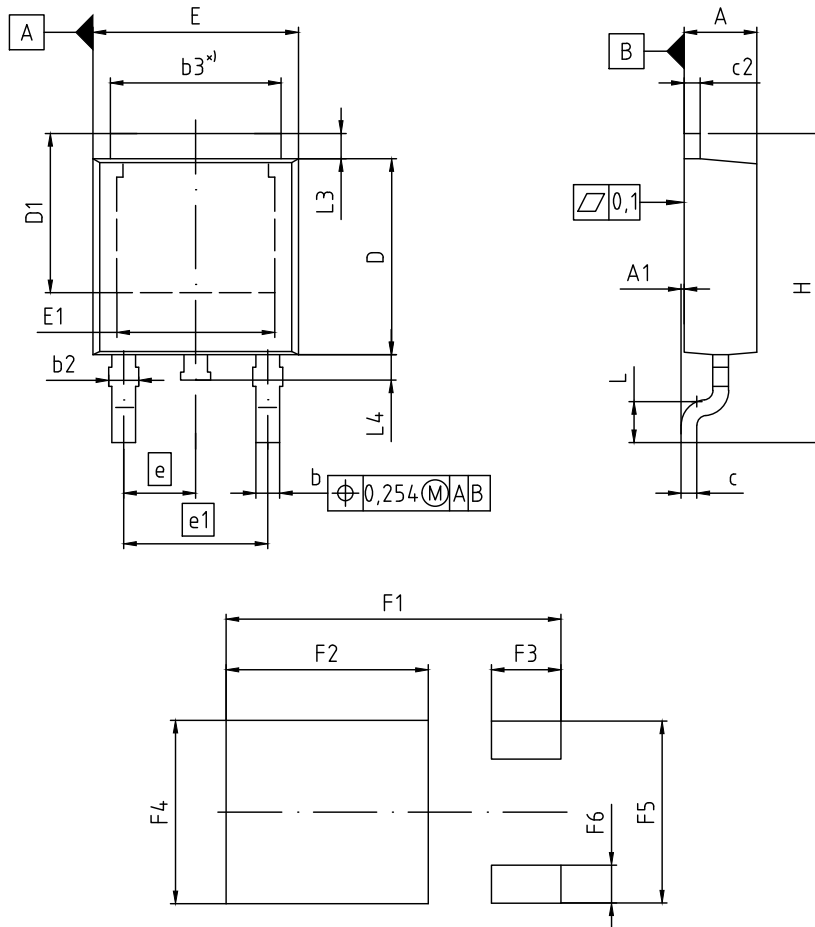
Table 9 Switching times

Switching times test circuit for inductive load	Switching times waveform

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

6 Package Outlines



*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.60	0.185	0.220
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57 (BSC)		0.180 (BSC)	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

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REVISION 05

Figure 1 Outline PG-TO 252, dimensions in mm/inches

600V CoolMOS™ CE Power Transistor
IPD60R2K1CE, IPU60R2K1CE

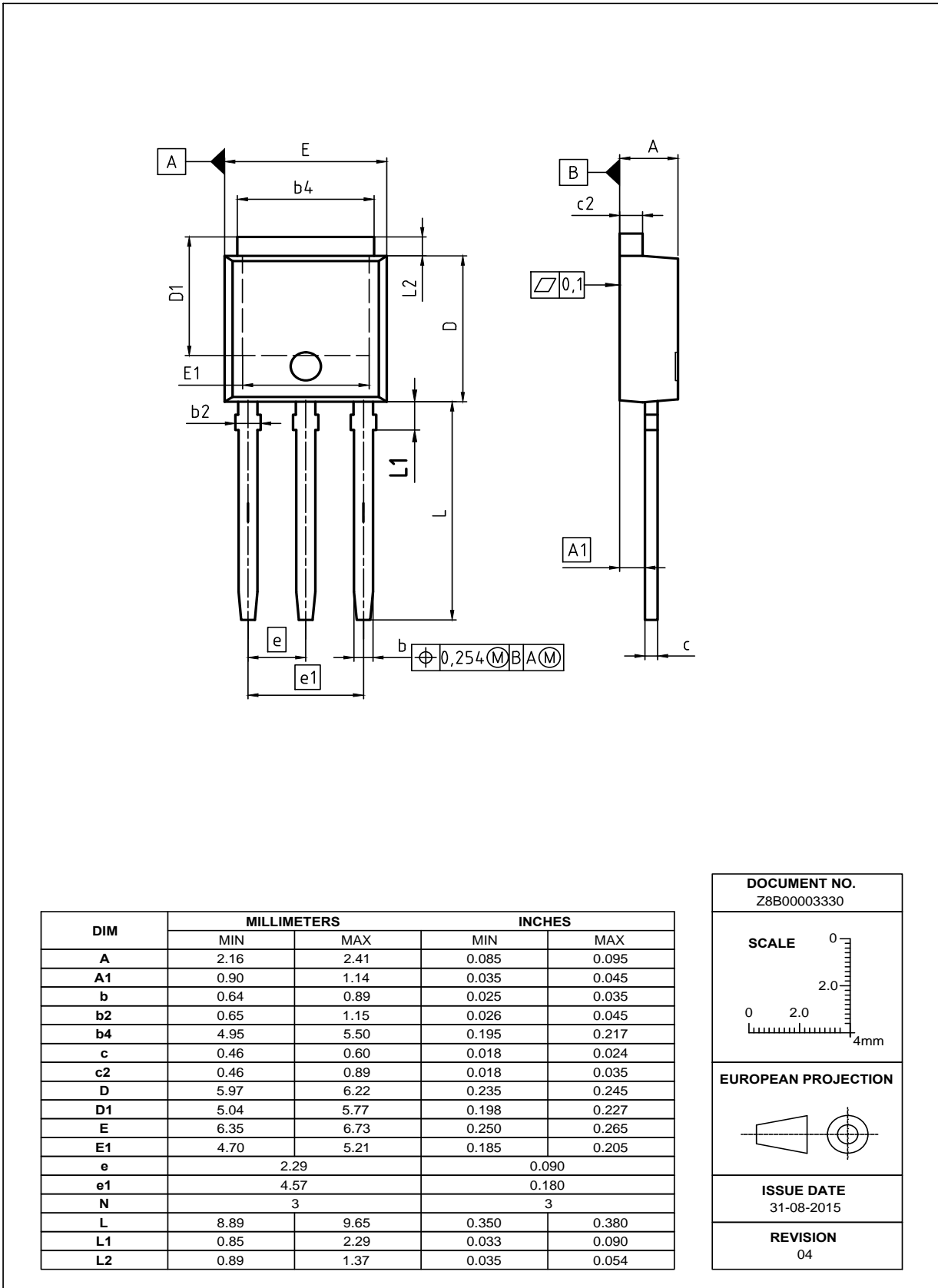


Figure 2 Outline PG-TO 251, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ CE Webpage: www.infineon.com
- IFX CoolMOS™ CE application note: www.infineon.com
- IFX CoolMOS™ CE simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPD60R2K1CE, IPU60R2K1CE

Revision: 2016-03-31

Previous Revision

Date	Subjects (major changes since last revision)
2014-09-25	Release of final version
2015-11-17	Updated with qualified for standard grade & updated package drawing
2016-03-31	Modified Id, Rthjc. Modified SOA, Zthjc curves

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